

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☑ Surface-mounted package
- ☑ Low Thermal Resistance

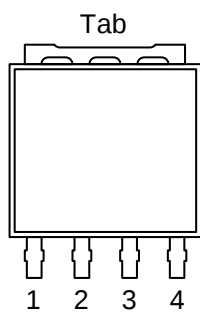
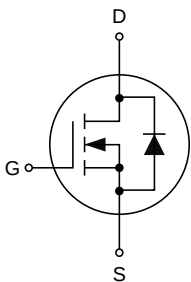
1.2 Applications

- ☑ Motor drivers
- ☑ DC/DC Converter

1.3 Quick reference

- ☑ $BV \geq 40\text{ V}$
- ☑ $R_{DS(ON)} \leq 1.1\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- ☑ $P_{tot} \leq 300\text{ W}$
- ☑ $R_{DS(ON)} \leq 2.9\text{ m}\Omega @ V_{GS} = 6\text{ V}$
- ☑ $I_D \leq 300\text{ A}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1,2,3	Source	 Top View LFPak 5x6	
4	Gate		
Tab	Drain		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}\text{C}$	-	40	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}\text{C}$	-	± 20	V
$I_{D^{*},**}$	Drain Current	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	300	A
		$T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	278	A
$I_{DM^{*},**}$	Pulsed Drain Current	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	1200	A
P_{tot}^{*}	Drain Power Dissipation	$T_C=25^{\circ}\text{C}$	-	300	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range		-55	175	$^{\circ}\text{C}$
I_S	Diode Forward Current	$T_C=25^{\circ}\text{C}$	-	300	A
E_{AS}^{*}	Single Pulsed Avalanche Energy	$V_{DD}=40\text{ V}, L=1.0\text{ mH}$	-	1436	mJ
$R_{\theta JA}^{*}$	Thermal Resistance-Junction to Ambient		-	65	$^{\circ}\text{C/W}$
$R_{\theta JC}^{*}$	Thermal Resistance-Junction to Case		-	0.5	

Notes:

- * Surface Mounted on 1 in² pad area, $t \leq 10\text{ sec}$
- ** Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- *** Limited by bonding wire

4. Marking Information

Product Name	Marking
KJ010N04LFH	KJ010N04H XXXXXX

5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ010N04LFH	LFPK 5x6	13 inch	-	5000	

Note: KJ010N04LFH defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C)

6. Electrical Characteristics (T_A=25°C Unless Otherwise Noted)

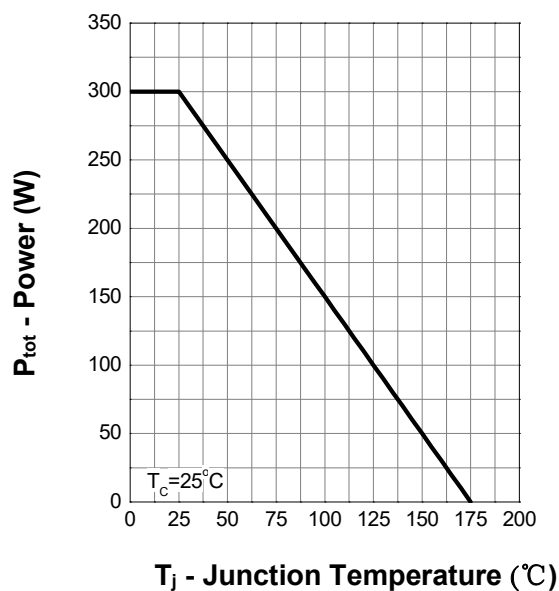
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	40	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	2.0	-	4.0	V
I _{DSS}	Drain Source Current	V _{DS} =32 V, V _{GS} =0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{GS} =±20 V, V _{DS} =0 V	-	-	±100	nA
R _{DS(ON)} ^a	On-State Resistance	V _{GS} =10 V, I _{DS} =30 A	-	0.96	1.1	mΩ
		V _{GS} =6 V, I _{DS} =20 A	-	2.2	2.9	
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =30 A, V _{GS} =0 V	-	-	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =30 A, V _{GS} =0 V, dI _{SD} /dt=100 A/μs	-	34	-	ns
Q _{rr}	Reverse Recovery Charge		-	25	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} =0 V, V _{DS} =20 V, Frequency=1 MHz	-	14272	-	pF
C _{oss}	Output Capacitance		-	916	-	
C _{rss}	Reverse Transfer Capacitance		-	280	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =20 V, V _{GEN} =10 V, R _G =3.9 Ω, R _L =0.66 Ω, I _{DS} =30 A	-	44	-	ns
t _r	Turn-on Rise Time		-	87	-	
t _{d(off)}	Turn-off Delay Time		-	113	-	
t _f	Turn-off Fall Time		-	55	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =20 V, V _{GS} =10 V, I _{DS} =30 A	-	217	-	nC
Q _{gs}	Gate-Source Charge		-	84	-	
Q _{gd}	Gate-Drain Charge		-	36	-	

Notes:

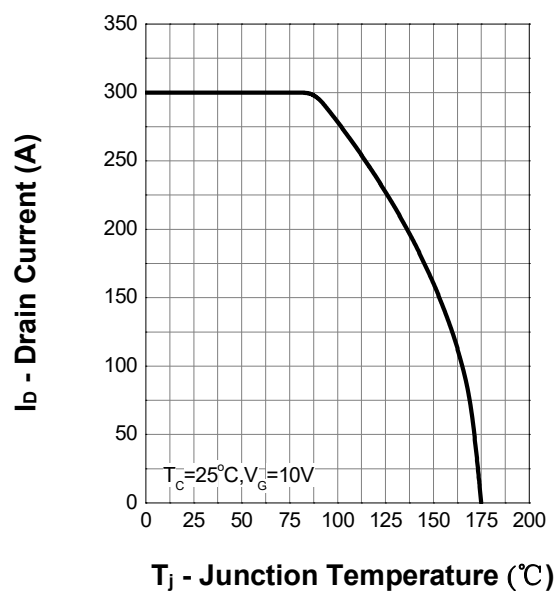
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%
- Guaranteed by design, not subject to production testing

7. Typical Characteristics

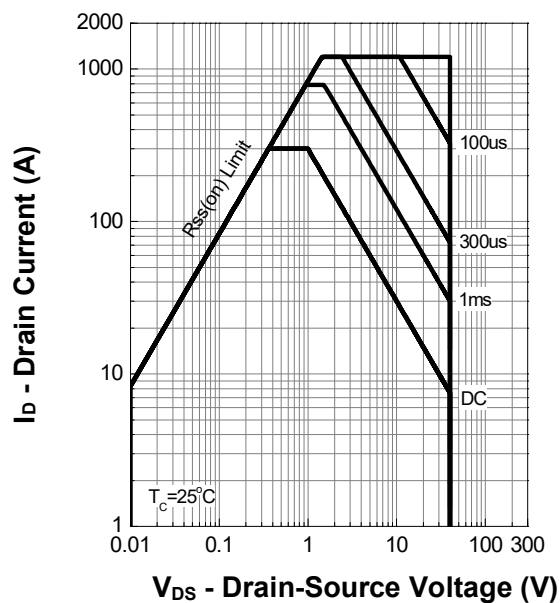
Power Capability



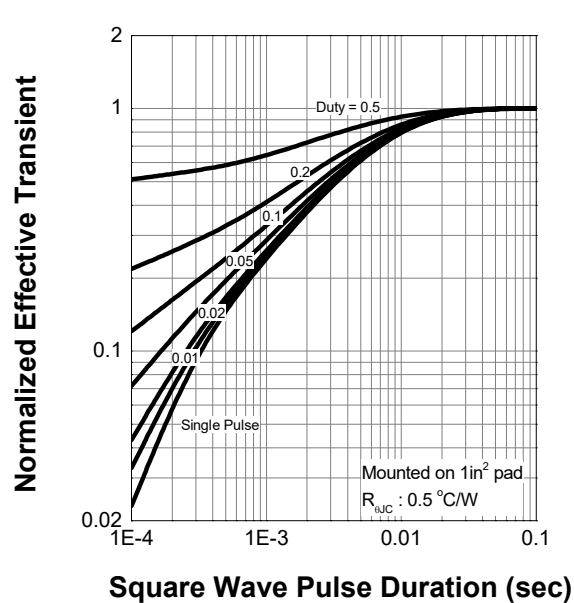
Current Capability



Safe Operation Area

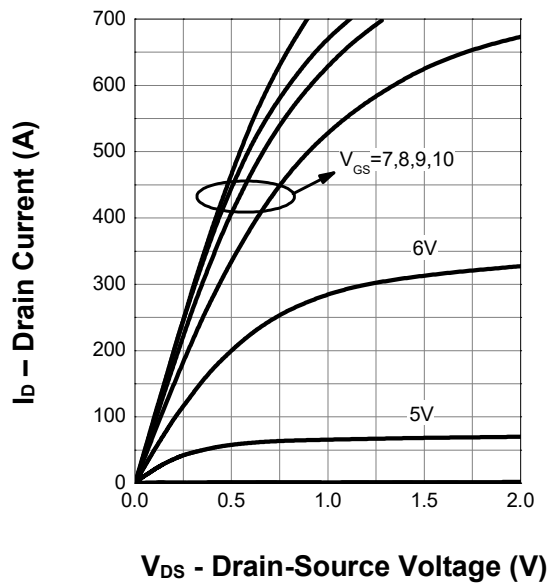


Thermal Transient Impedance

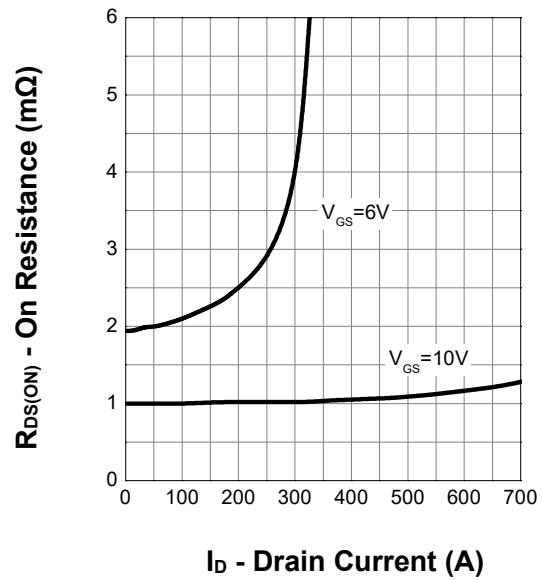


7. Typical Characteristics (Cont.)

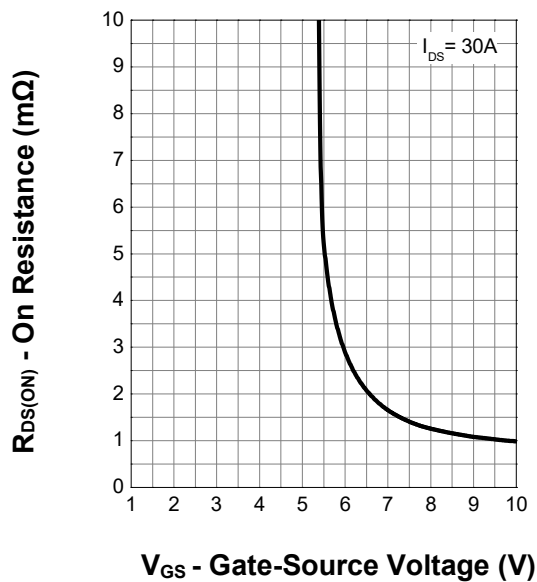
Output Characteristics



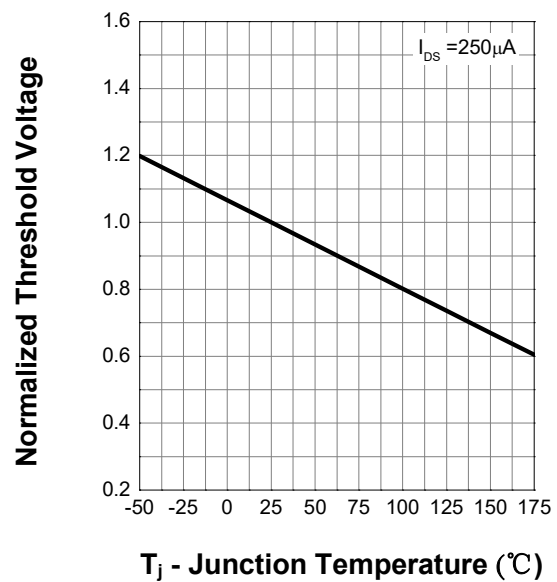
Drain-Source On Resistance



Transfer Characteristics

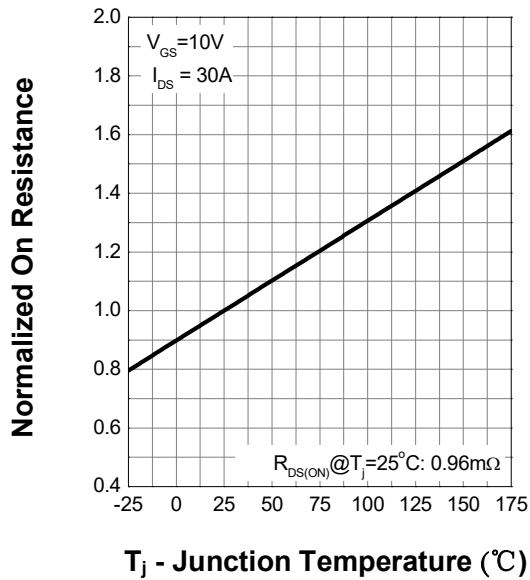


Gate Threshold Voltage

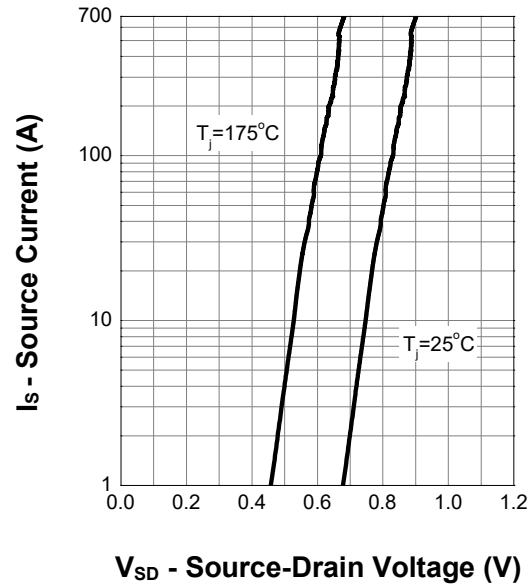


7. Typical Characteristics (Cont.)

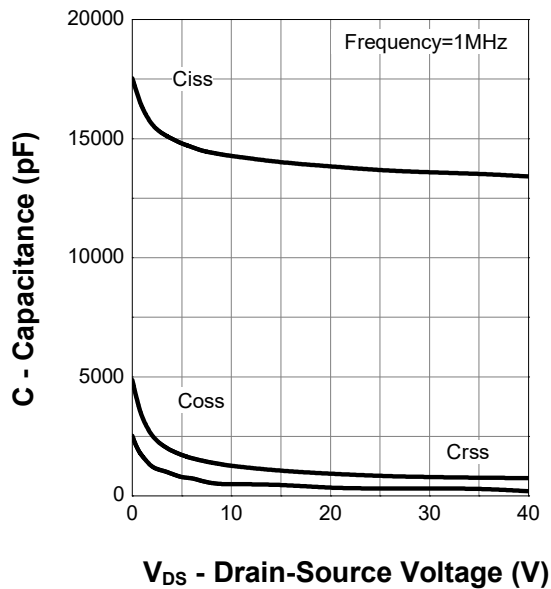
Drain-Source On Resistance



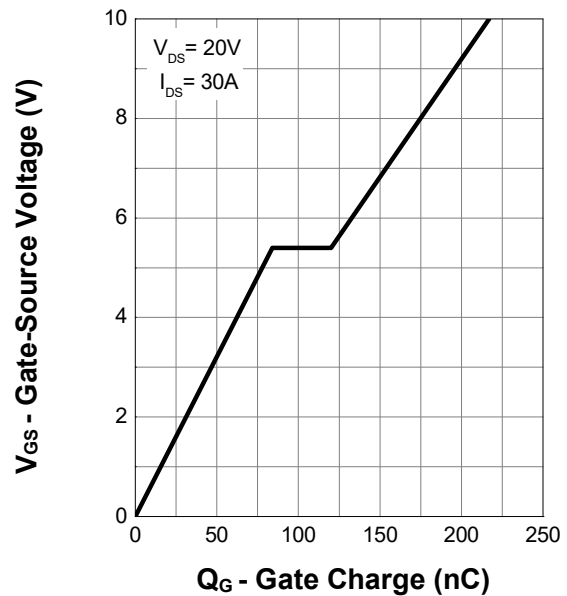
Body Diode Characteristics



Capacitance

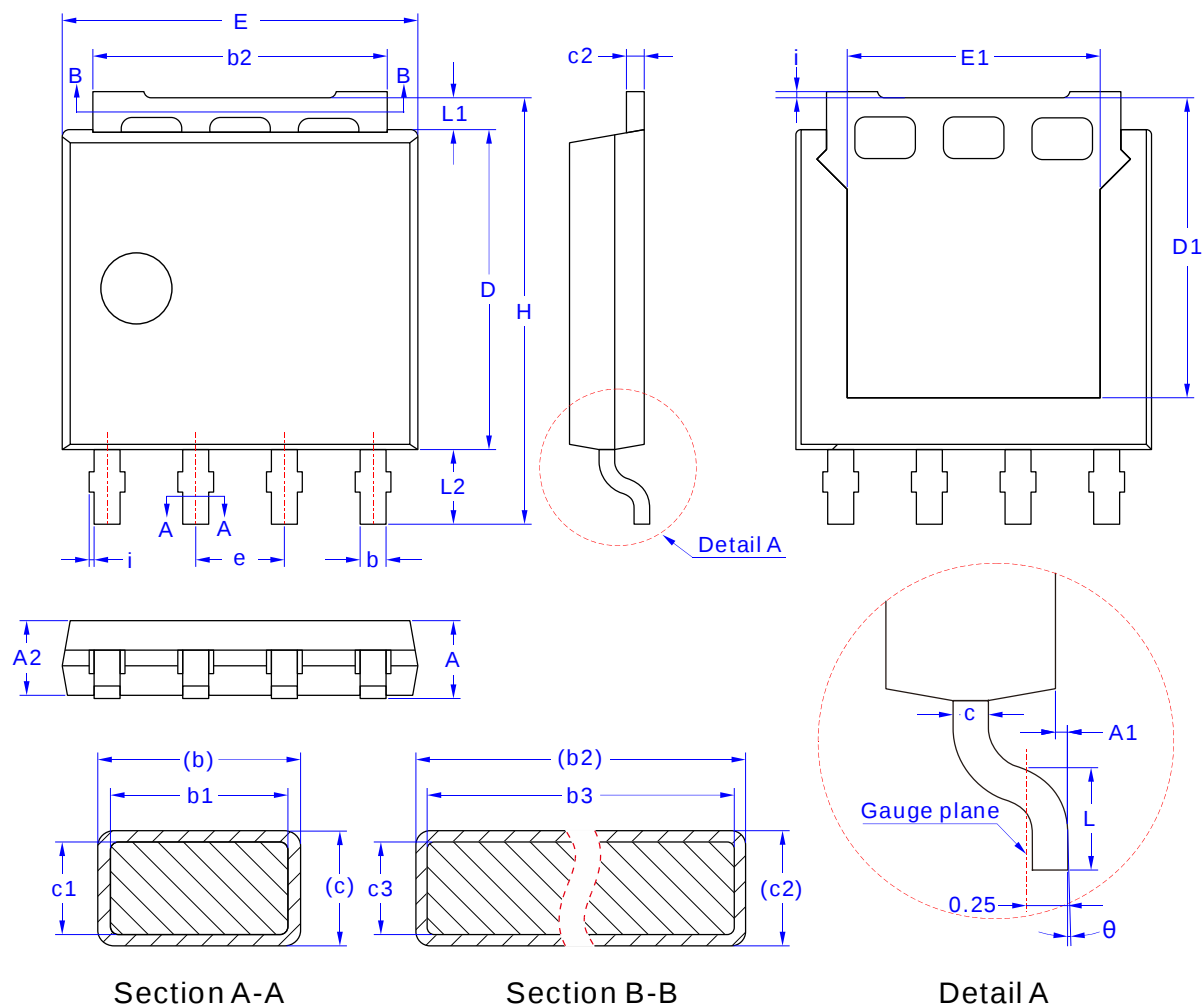


Gate Charge



8. Package Dimensions

LFPAK 5x6 Package



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.00	1.30
A1	0	0.15
A2	0.98	1.12
b	0.35	0.50
b1	0.32	0.46
b2	4.02	4.41
b3	4.00	4.37
c	0.19	0.25
c1	0.17	0.23
c2	0.24	0.30
c3	0.22	0.28

Symbol	Dimensions in Millimeters	
	MIN.	MAX.
D	4.45	4.70
D1	-	4.45
E	4.95	5.30
E1	3.50	3.70
e	1.27 BSC	
H	5.95	6.25
i	-	0.25
L	0.40	0.85
L1	0.27	0.57
L2	0.80	1.30
θ	0°	8°